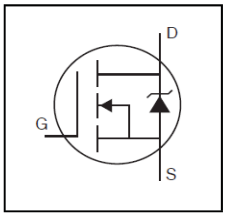
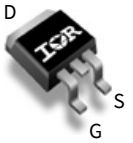
特性

- 先进平面技术
- 低电平导通电阻
- 动态 dV/dT 和 dI/dT 能力
- 工作温度 175°C
- 快速开关
- 雪崩完全额定
- 允许达到 Tjmax 的重复雪崩
- 无铅，符合RoHS要求
- 汽车认证 *



V_{DSS}	55V
$R_{DS(on)}$ max.	17.5mΩ
I_D	49A



D^2-Pak

AUIRFZ44NS

描述

这款 HEXFET®功率MOSFET专为汽车应用而设计，采用最新的工艺技术实现单位硅面积极低的导通电阻。该设计的其他特点包括175°C工作结温、开关速度快和提高重复雪崩额定值。通过结合以上特点，使该设计成为一种极其高效和可靠的器件，可用于汽车应用和各种其他应用。

G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRFZ44NS	D^2-Pak	Tube	50	AUIRFZ44NS
		Tape and Reel Left	800	AUIRFZ44NSTRL

绝对最大额定值

超过“绝对最大额定值”所列值的应力可能会对器件造成永久性损坏。这些仅仅是应力额定值，并不意味着器件在这些或任何其他超过该规范所示的条件下能够正常运行。延长暴露在绝对最大额定值条件的时间可能会影响器件的可靠性。热阻抗和功率耗散额定值是在装板和静止空气条件下测得的。环境温度（TA）为 25°C，除非另有规定。

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	49	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	35	
I_{DM}	Pulsed Drain Current ①	160	
P_D @T_A = 25°C	Maximum Power Dissipation	3.8	W
P_D @T_C = 25°C	Maximum Power Dissipation	94	
	Linear Derating Factor	0.63	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
$E_{AS\ (Thermally\ Limited)}$	Single Pulse Avalanche Energy (Thermally Limited) ⑥	150	mJ
$E_{AS\ (Tested)}$	Single Pulse Avalanche Energy (Tested Limited) ⑤	530	
I_{AR}	Avalanche Current ①	25	A
E_{AR}	Repetitive Avalanche Energy ①	9.4	mJ
dv/dt	Peak Diode Recovery ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

热阻抗

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	1.5	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount), D^2 Pak	---	40	

HEXFET®是英飞凌的注册商标。

*认证标准可在 www.infineon.com 上找到

本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。为确认准确性，请务必访问 infineon.com 参考最新的英文版本（控制文档）。

静态参数特性在 T_J = 25°C 时测得（除非另有规定）

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	---	---	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	---	0.058	---	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	---	---	17.5	mΩ	V_{GS} = 10V, I_D = 25A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	---	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
gfs	Forward Trans conductance	19	---	---	S	V_{DS} = 25V, I_D = 25A
I_{DSS}	Drain-to-Source Leakage Current	---	---	25	μA	V_{DS} = 55V, V_{GS} = 0V
		---	---	250		V_{DS} = 44V,V_{GS} = 0V,T_J =150°C
I_{GSS}	Gate-to-Source Forward Leakage	---	---	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	---	---	-100		V_{GS} = -20V

动态电气特性在 T_J = 25°C时测得（除非另有规定）

Q_g	Total Gate Charge	---	---	63	nC	I_D = 25A V_{DS}
Q_{gs}	Gate-to-Source Charge	---	---	14		= 44V
Q_{gd}	Gate-to-Drain Charge	---	---	23		V_{GS} = 10V, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	---	12	---	ns	V_{DD} = 28V I_D
t_r	Rise Time	---	60	---		= 25A R_G=
$t_{d(off)}$	Turn-Off Delay Time	---	44	---		12Ω
t_f	Fall Time	---	45	---		V_{GS} = 10V, See Fig. 10 ④
L_D	Internal Drain Inductance	---	4.5	---	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	---	7.5	---		
C_{iss}	Input Capacitance	---	1470	---	pF	V_{GS} = 0V V_{DS}
C_{oss}	Output Capacitance	---	360	---		= 25V
C_{rss}	Reverse Transfer Capacitance	---	88	---		f = 1.0MHz, See Fig. 5

二极管特性

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	---	---	49	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	---	---	160		
V_{SD}	Diode Forward Voltage	---	---	1.3	V	T_J = 25°C,I_S = 25A,V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	---	63	95	ns	T_J = 25°C ,I_F = 25A
Q_{rr}	Reverse Recovery Charge	---	170	260	nC	di/dt = 100A/μs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

注：

① 重复额定值；脉冲宽度受最高结温限制。（见图11）

② 受 T_{Jmax} 限制，初始 T_J = 25°C、L = 0.48mH、R_G = 25 Ω 、I_{AS} = 25A、V_{GS} =10V。（见图 12）

③ I_{SD} ≤ 25A, di/dt ≤ 230A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 175°C.

④ 脉冲宽度≤ 400μs；占空比≤ 2%。

⑤ 这是器件损坏时的典型值，代表超出额定限制的操作。

⑥ 这是一个计算值，限制在 T_J = 175°C 的条件下。

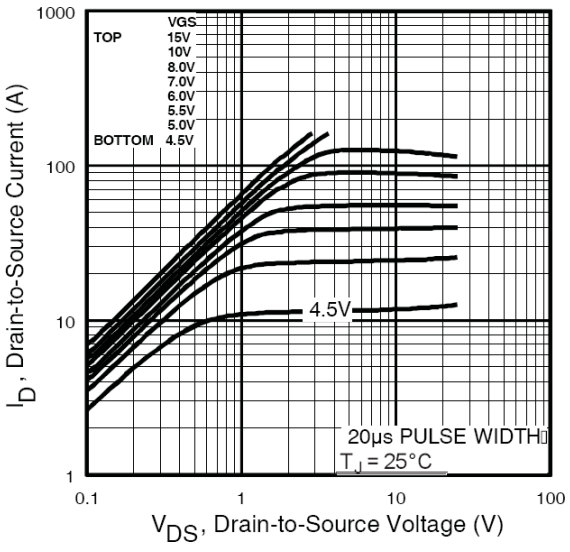


图 1典型输出特性

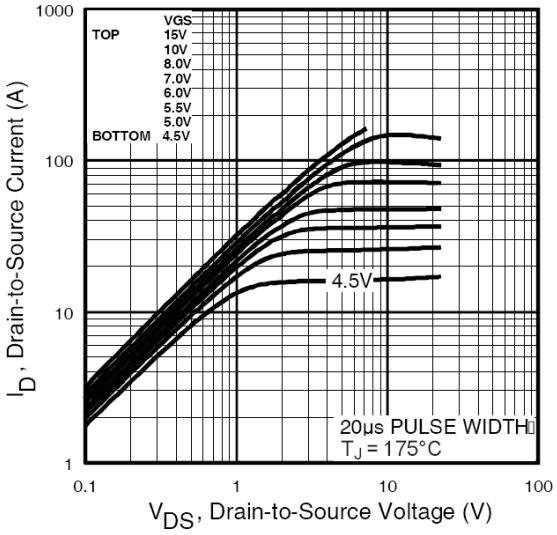


图 2典型输出特性

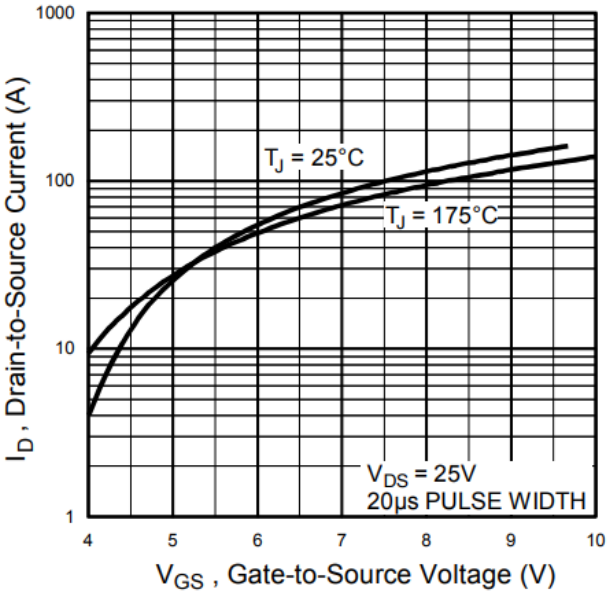


图 3典型转移特性

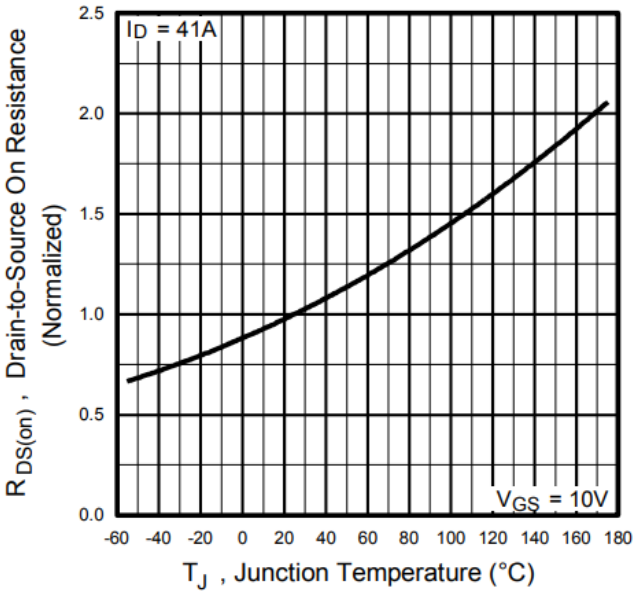


图4归一化导通电阻与温度的关系曲线

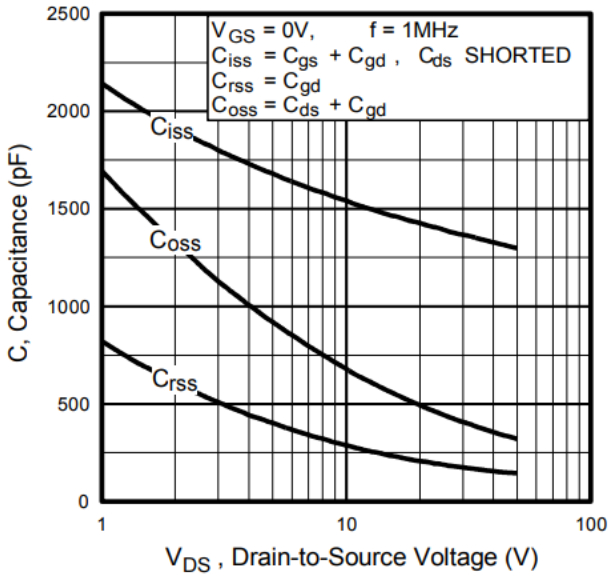


图 5.典型电容值与漏源电压的关系

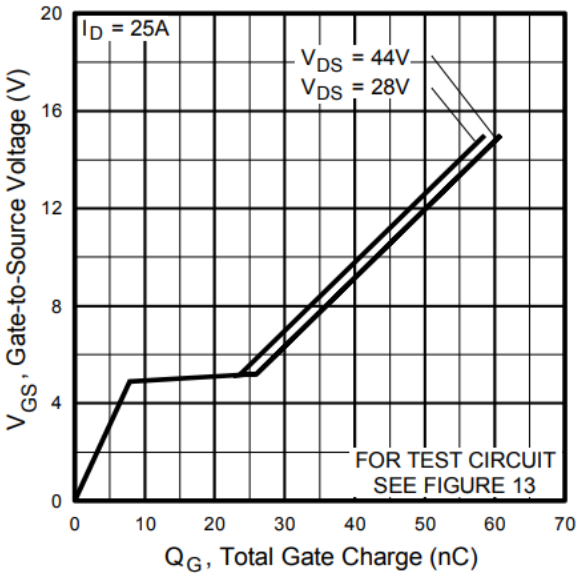


图 6.典型栅极电荷与栅源电压的关系

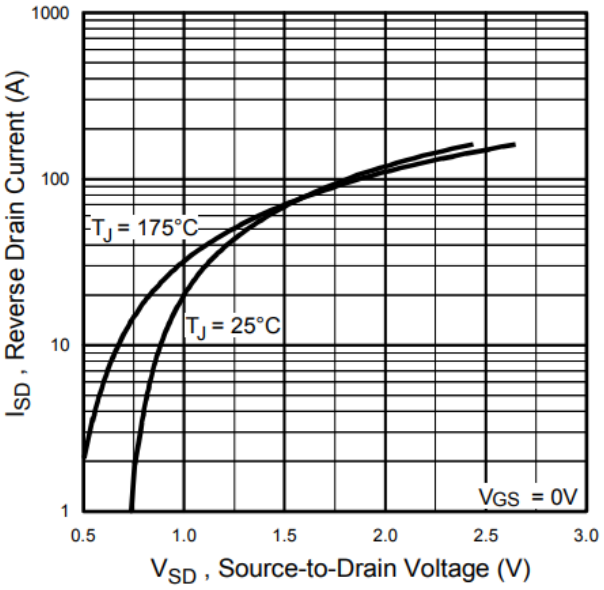


图 7典型源漏二极管正向电压

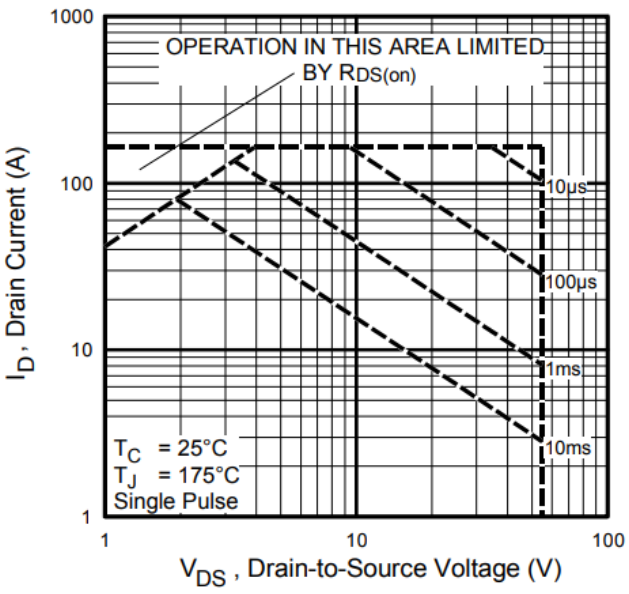


图 8.最大安全工作区

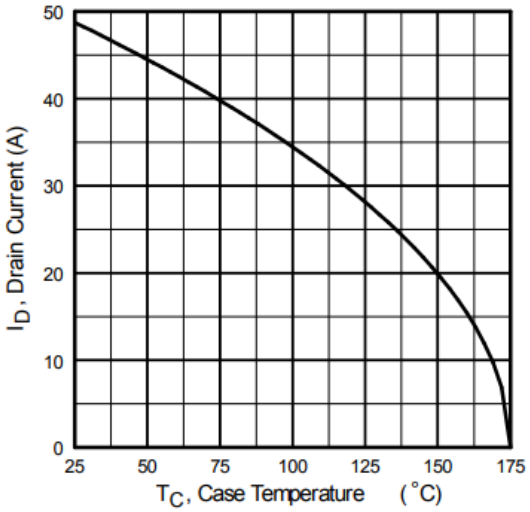


Fig 9. Maximum Drain Current vs. Case Temperature

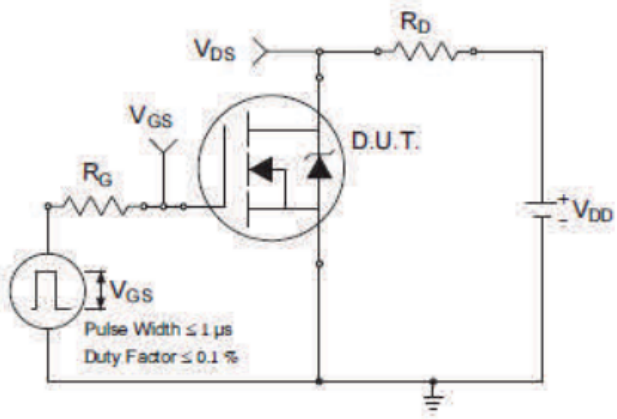


Fig 10a. Switching Time Test Circuit

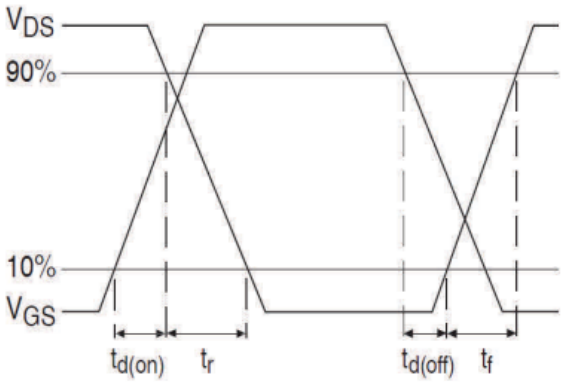


Fig 10b. Switching Time Waveforms

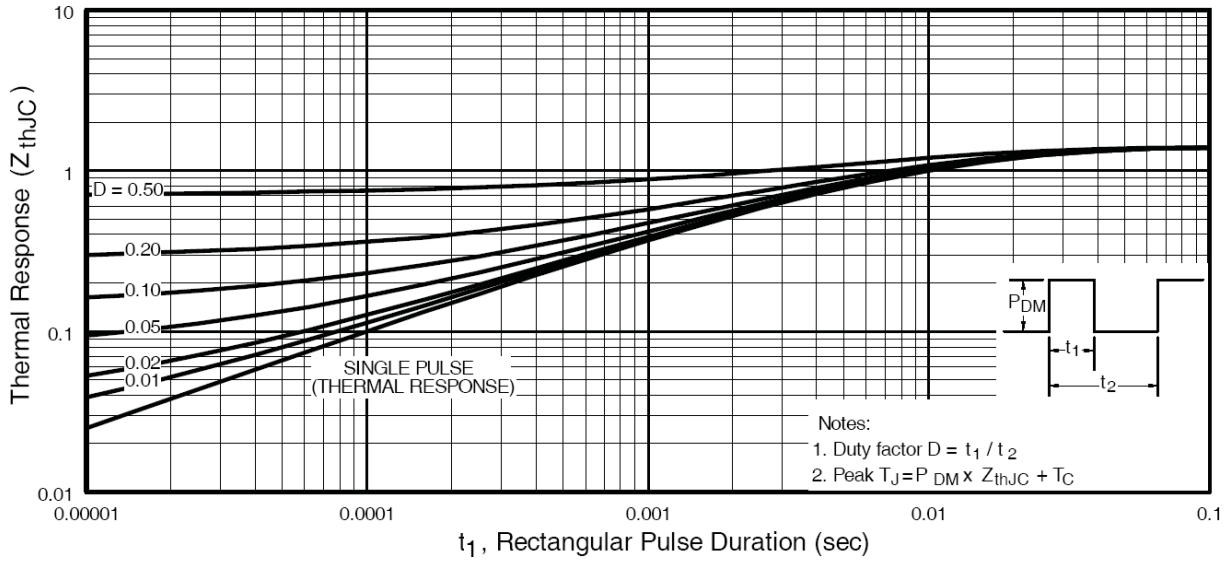


图 11.最大有效瞬态热阻，结到壳

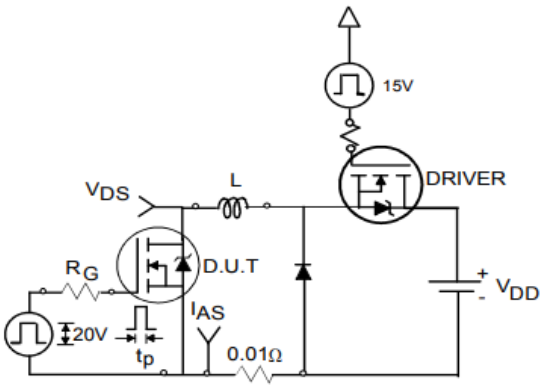


Fig 12a. Unclamped Inductive Test Circuit

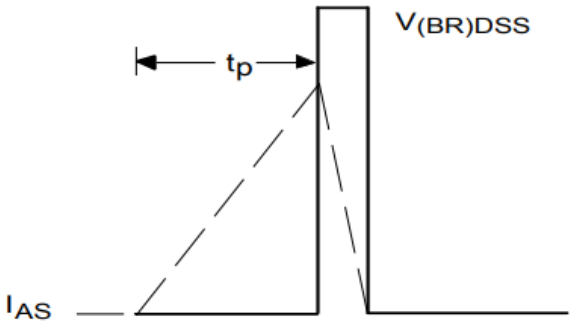


Fig 12b. Unclamped Inductive Waveforms

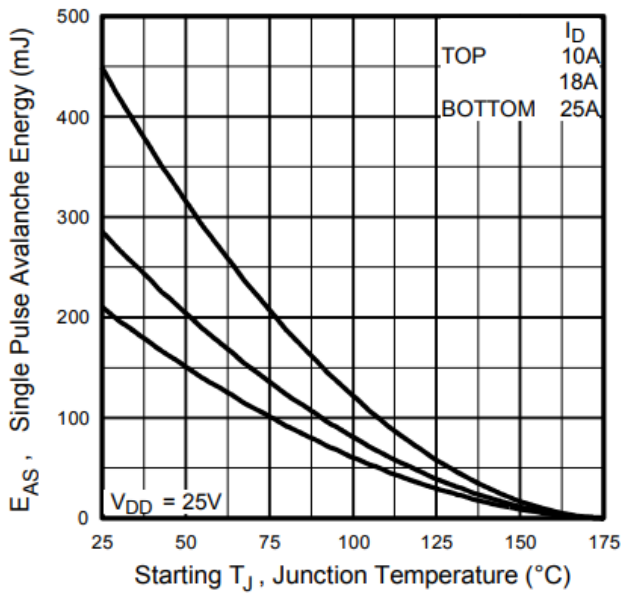


Fig 12c. Maximum Avalanche Energy vs. Drain Current

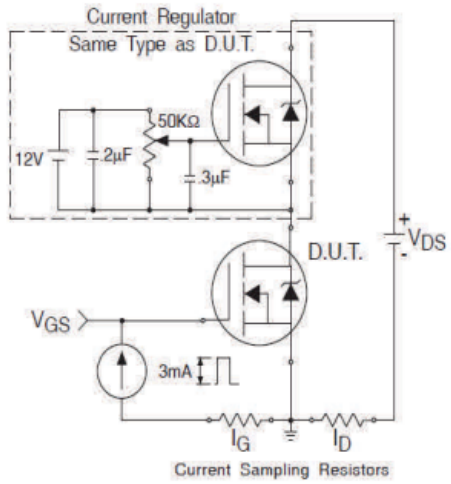


Fig 13a. Gate Charge Test Circuit

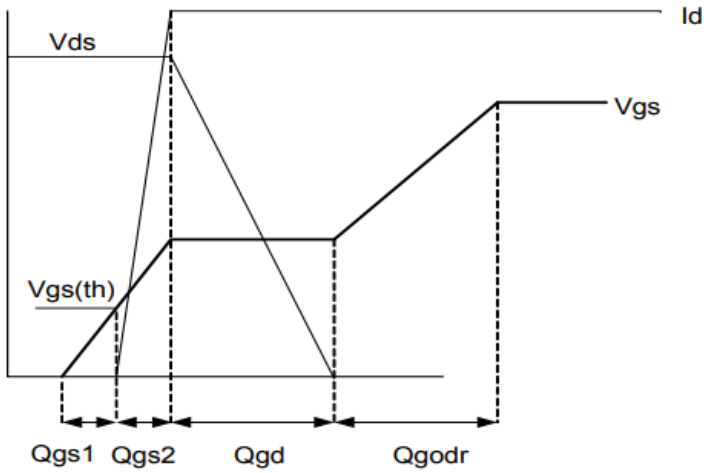


Fig 13b. Gate Charge Waveform

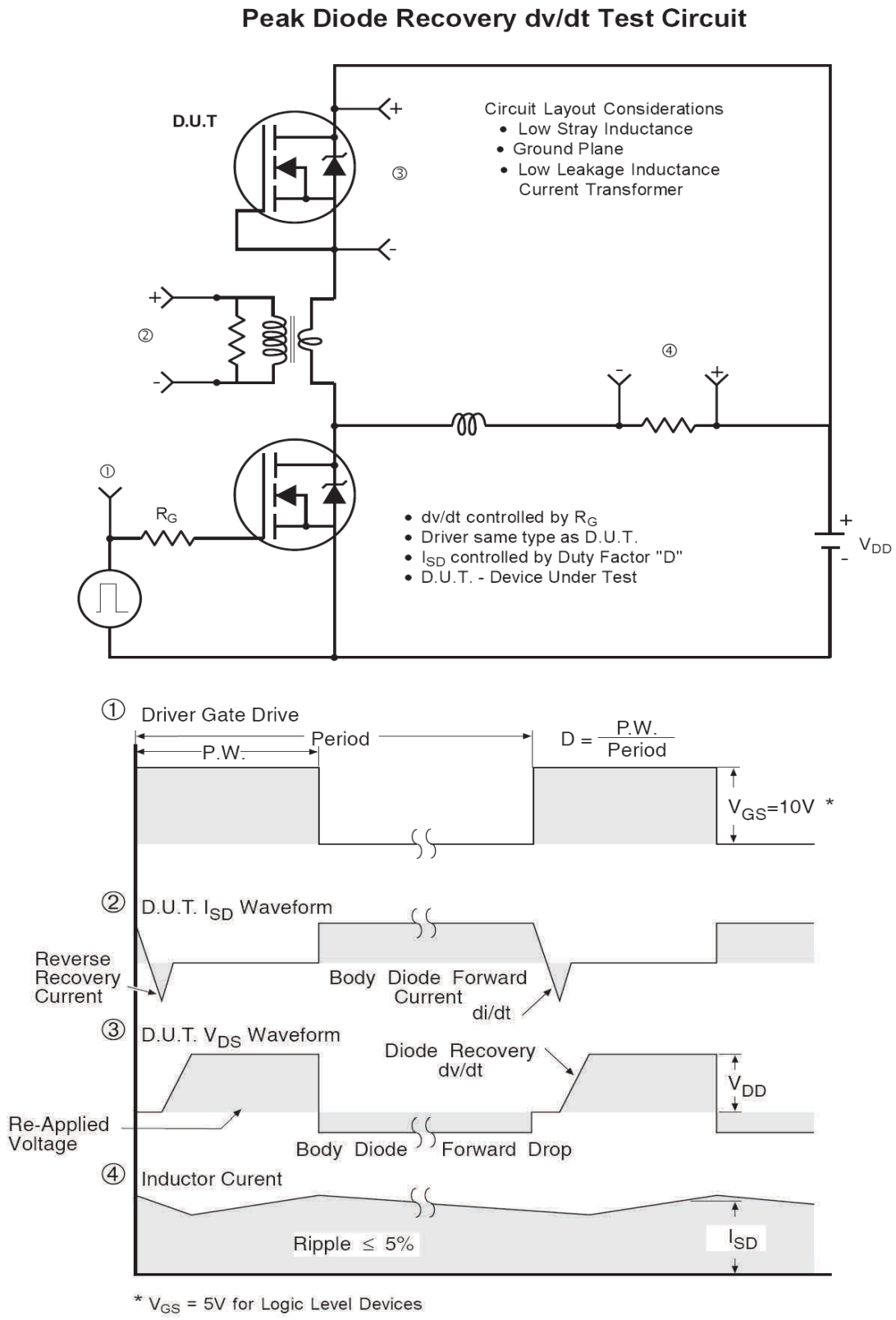
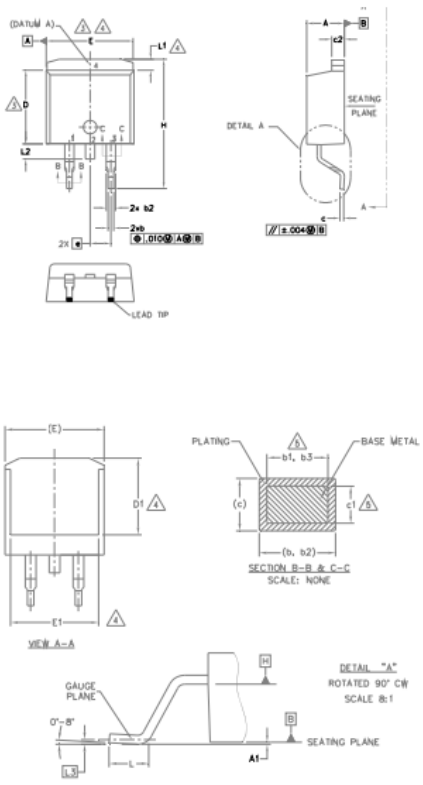


图 14. N 沟道 HEXFET® 功率 MOSFET 体内二极管峰值恢复 dv/dt 测试电路

D ² Pak (TO-263AB) 封装外形（尺寸以毫米（英寸）为单位）



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1, b3 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	–	.270	–	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	–	.245	–	4
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	–	1.68	–	.066	4
L2	–	1.78	–	.070	
L3	0.25 BSC		.010 BSC		

LEAD ASSIGNMENTS

DIODES

1.– ANODE (TWO DIE) / OPEN (ONE DIE)
2, 4.– CATHODE
3.– ANODE

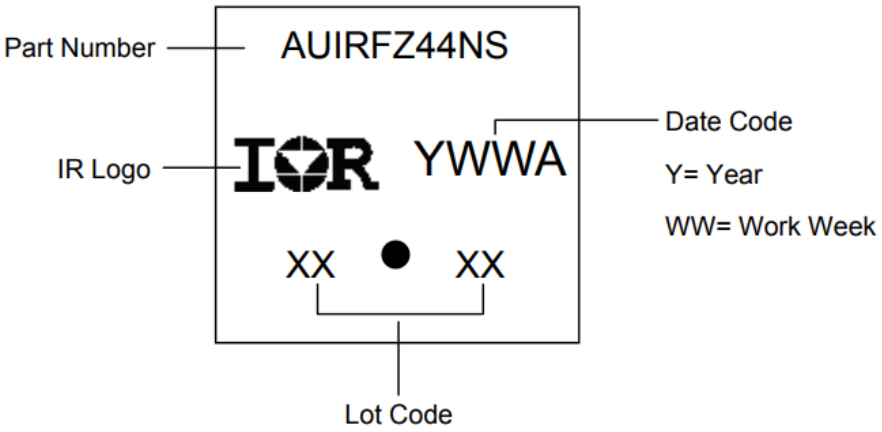
HEXFET

1.– GATE
2, 4.– DRAIN
3.– SOURCE

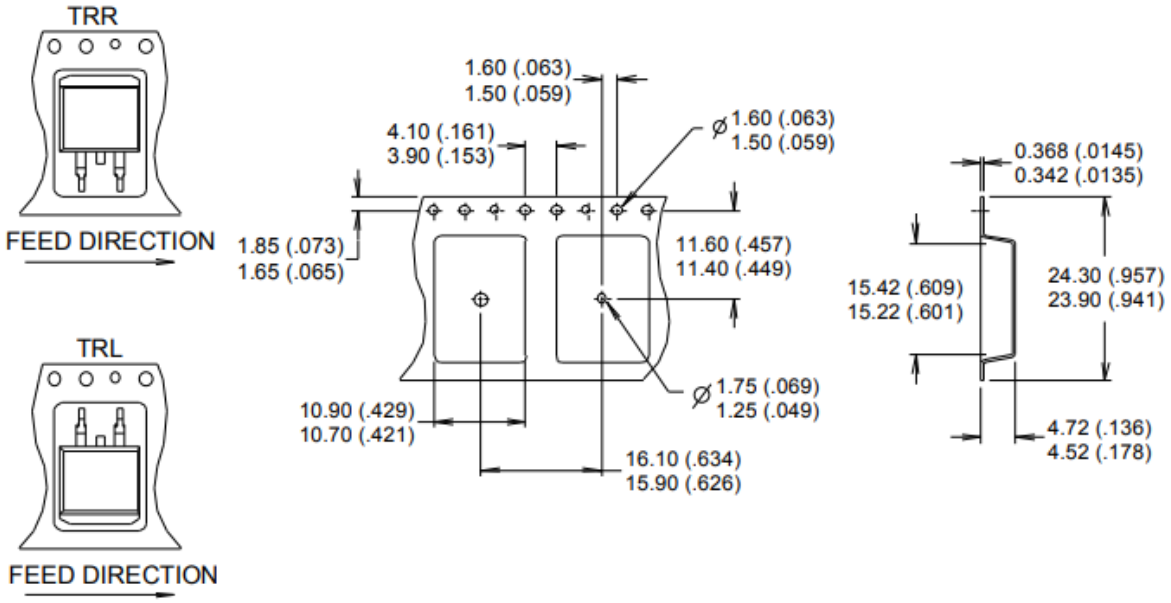
IGBTs, CoPACK

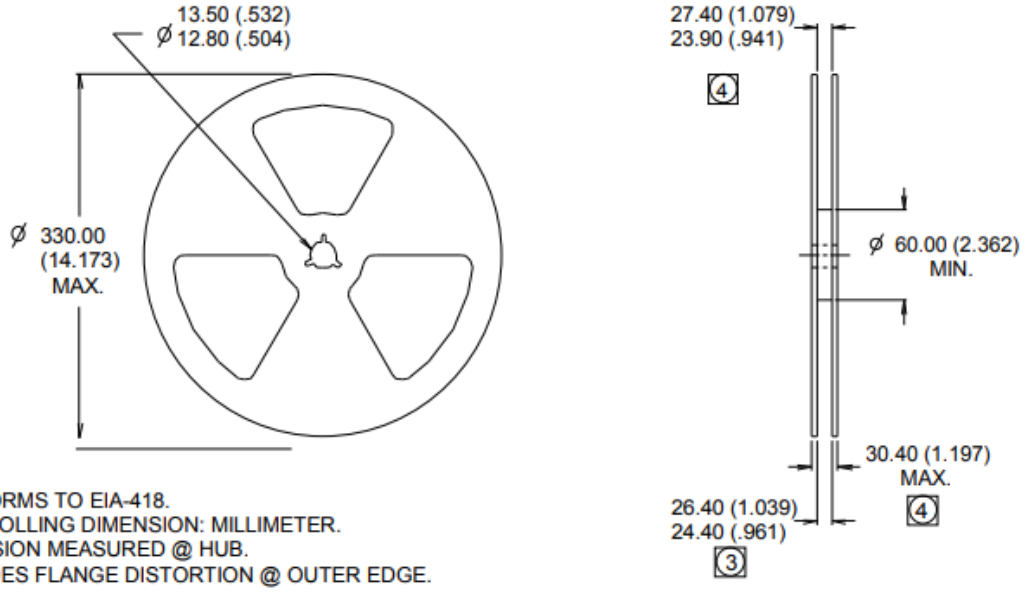
1.– GATE
2, 4.– COLLECTOR
3.– EMITTER

D ² Pak（TO-263AB）零件信息标识



D ² Pak（TO-263AB）卷、带信息（尺寸以毫米（英寸）为单位）





NOTES :
1. COMFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Qualification Information

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		D^2-Pak	MSL1
ESD	Machine Model	Class M3 (+/- 400V)† AEC-Q101-002	
	Human Body Model	Class H1B (+/- 1000V)† AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V)† AEC-Q101-005	
RoHS Compliant		Yes	

† 最高通过电压。

修订记录

Date	Comments
10/27/2015	• Updated datasheet with corporate template • Corrected ordering table on page 1.
10/25/2017	• Removed TO-262 Pak "AUIRFSL3207Z" this devices TO-262 Pak was never released and this part was erroneously added to the datasheet. –All pages • Corrected typo error on part marking on page 8.

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